

**Vishay Siliconix** 

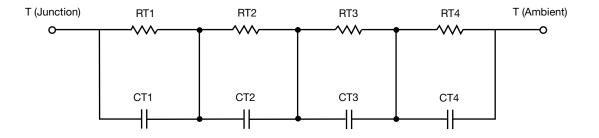
# **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	N/A	102.1750m	N/A		
RT2	N/A	189.4508m	N/A		
RT3	N/A	183.5544m	N/A		
RT4	N/A	124.2924m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	5.4032m	N/A		
CT2	N/A	355.2337m	N/A		
CT3	N/A	375.6587m	N/A		
CT4	N/A	19.0201m	N/A		

Note

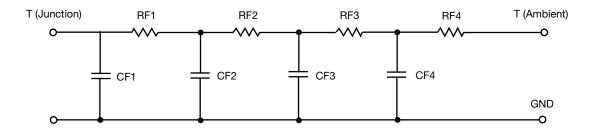
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	N/A	218.7252m	N/A		
RF2	N/A	164.6040m	N/A		
RF3	N/A	97.6395m	N/A		
RF4	N/A	118.6003m	N/A		
·	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	4.7660m	N/A		
CF2	N/A	121.5478m	N/A		
CF3	N/A	114.6766m	N/A		
CF4	N/A	79.5019m	N/A		

Note

• n/a indicates not applicable



# SiHG14N50D\_RC

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